

P-Channel 20-V (G-S) MOSFET

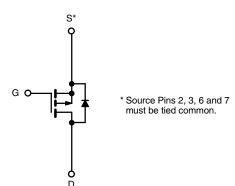
PRODUCT	SUMMARY	
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)
	0.012 at V _{GS} = - 4.5 V	- 9.0
-20	0.015 at V _{GS} = - 2.5 V	- 7.8
	0.020 at V _{GS} = - 1.8 V	- 6.0

FEATURES

- Halogen-free
- TrenchFET[®] Power MOSFETs



TSSOP-8 D S 8 D 1 7 S 6 S 5 D s З G Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	A = 25 °C, unles	ss otherwise no	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	-2	20	V
Gate-Source Voltage		V _{GS}	±	: 12	v
	T _A = 25 °C		- 9.0	-7.8	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	- ^I D	- 6.8	-5.8	
Pulsed Drain Current (10 µs Pulse Width)	·	I _{DM}	-	30	A
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 1.35	- 0.95	
	T _A = 25 °C	P _D	1.5	1.05	W
Maximum Power Dissipation ^a	T _A = 70 °C	L L L	1.0	0.67	vv
Operating Junction and Storage Temperature Range	Э	T _J , T _{stg}	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum lungtion to Ambienta	$t \le 10 s$	R _{thJA}	65	83	
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	43	52	

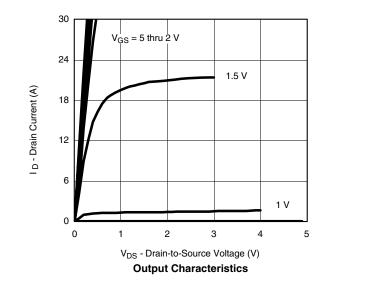
Notes: a. Surface Mounted on 1" x 1" FR4 board.

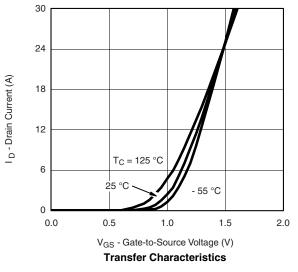
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -450 \ \mu A$	- 0.45	-	1.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$			± 100	nA	
Zaus Cata Malta na Dusia Cuurant		$V_{DS} = -20 V, V_{GS} = 0 V$			- 1		
Zero Gate Voltage Drain Current	IDSS	V_{DS} = -20V, V $_{GS}$ = 0 V, T _J = 70 °C			- 25	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -4.5 V$	- 20			А	
		V _{GS} = - 4.5 V, I _D = - 8.0 A		0.010			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 7.0 A		0.012		Ω	
		V _{GS} = - 1.8 V, I _D = - 5.8 A		0.016			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 8.0 A		44		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.5 A, V _{GS} = 0 V		- 0.56	- 1.1	V	
Dynamic ^b	-						
Total Gate Charge	Qg			46	70		
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 8.0 A		5		nC	
Gate-Drain Charge	Q _{gd}			15.5			
Turn-On Delay Time	t _{d(on)}			45	70		
Rise Time	t _r	V_{DD} = - 10 V, P = 6 Ω		85	130		
Turn-Off Delay Time	t _{d(off)}	${\rm I_D}\cong$ - 1 A, ${\rm V_{GEN}}$ = - 4.5 V, ${\rm R_g}$ = 6 Ω		220	400	ns	
Fall Time	t _f			155	235		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.5 A, di/dt = 100 A/μs		140	210		

Notes: a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

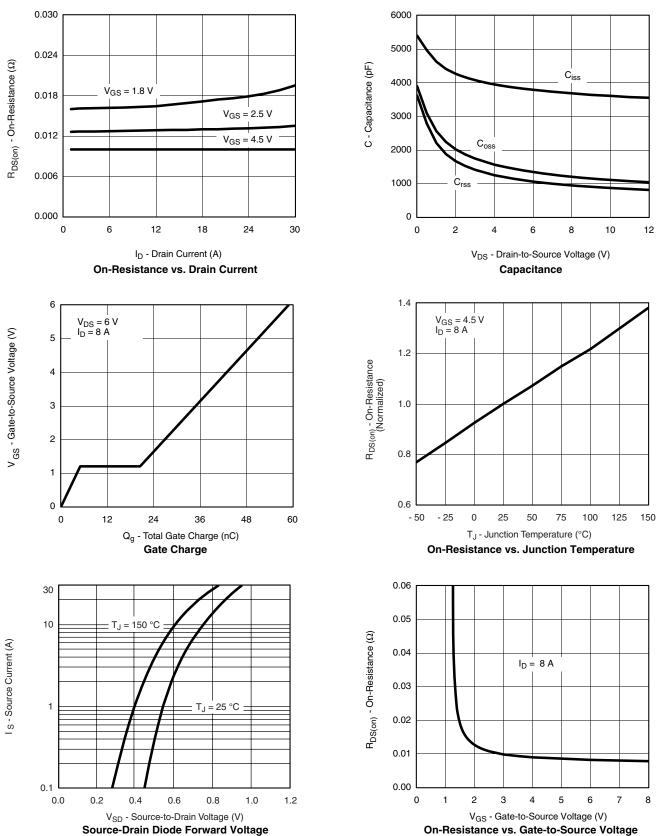




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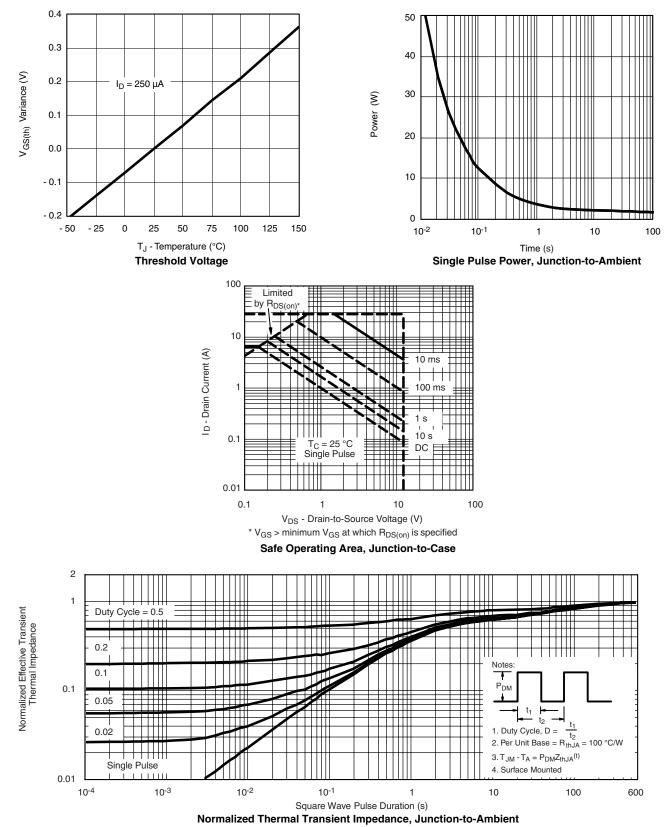






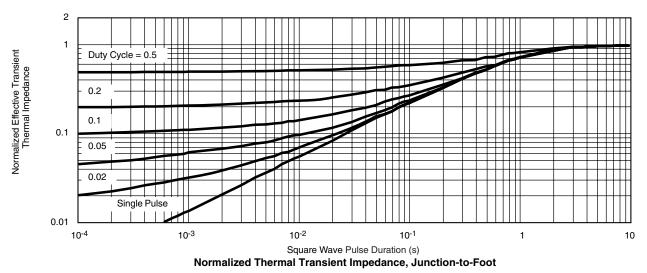


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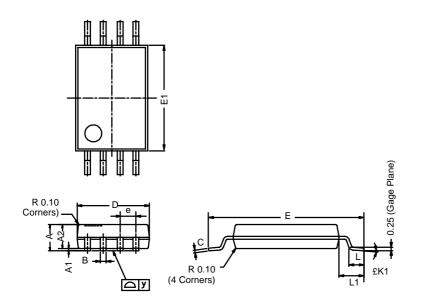


SI6435ADQ-T1-GE3



TSSOP: 8-LEAD

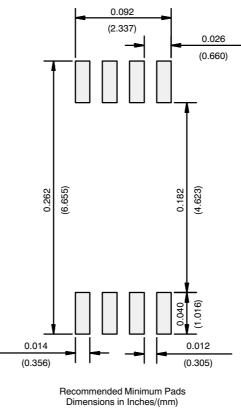
JEDEC Part Number: MO-153



Dim	MILLIMETERS			
	Min	Nom	Max	
Α	-	I	1.20	
A ₁	0.05	0.10	0.15	
A ₂	0.80	1.00	1.05	
В	0.19	0.28	0.30	
С	-	0.127	-	
D	2.90	3.00	3.10	
Е	6.20	6.40	6.60	
E ₁	4.30	4.40	4.50	
е	-	0.65	-	
L	0.45	0.60	0.75	
L ₁	0.90	1.00	1.10	
Y	-	-	0.10	
£ K1	0°	3°	6°	



RECOMMENDED MINIMUM PADS FOR TSSOP-8





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